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Electrical Properties and Crystallographic Characterization of Gd₂O₃ Doped Bi₂O₃ Polymorphs.

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The main aims of this study are to determine new phases of bismuth trioxide gadolinium trioxide binary system and the temperature dependence of the electrical transport properties. The reaction products obtained in an open air atmosphere were characterized by X-ray powder diffractions (XRD) and the unit cell parameters were calculated by using the diffraction patterns. The $\alpha+\beta$ -Bi₂O₃, β -Bi₂O₃ and $\beta+\delta$ -Bi₂O₃ crystal system were obtained by doping 0,01 ≤ %Gd₂O₃ ≤ 0,02 mole, 0,02 ≤ %Gd₂O₃ ≤ 0,07 mole and 0,08 ≤ %Gd₂O₃ ≤ 0,15 mole (at 750oC), respectively. The $\alpha+\beta$ -Bi₂O₃, β -Bi₂O₃ and δ -Bi₂O₃ crystal system were obtained by doping 0,01 ≤ % Gd₂O₃ ≤ 0,04 mole, 0,05 ≤ %Gd₂O₃ ≤ 0,08 mole and 0,09 ≤ %Gd₂O₃ ≤ 0,15 mole (at 760oC,quench), respectively. The $\alpha+\beta$ -Bi₂O₃ and δ -Bi₂O₃ crystal system were obtained by doping 0,01 ≤ %Gd₂O₃ ≤ 0,08 mole, 0,09 ≤ %Gd₂O₃ ≤ 0,15 mole (at 810oC, quench), respectively. Thermal behavior and thermal stability of the phases were investigated by thermal analysis techniques. The temperature dependence of the electrical properties of β -Bi₂O₃ solid solution and of δ -Bi₂O₃ solid solution was measured by four point probe method.

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